

N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
100	0.040 at V _{GS} = 10 V	6.4	23 nC
	0.047 at V _{GS} = 8 V	5.5	

FEATURES

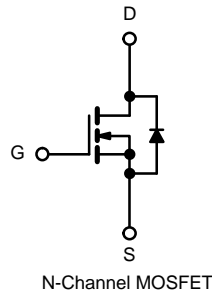
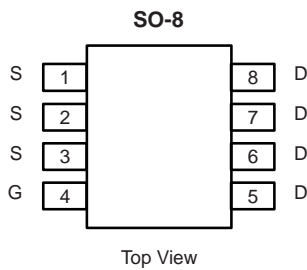
- Halogen-free According to IEC 61249-2-21 Definition
- Extremely Low Q_{gd} for Switching Losses
- 100 % R_g Tested
- 100 % Avalanche Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Primary Side Switch



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	100	V	
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	6.4	A
		T _C = 70 °C	5.1	
		T _A = 25 °C	5.5 ^{b, c}	
		T _A = 70 °C	4.5 ^{b, c}	
Pulsed Drain Current	I _{DM}	26		
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	4.5	
		T _A = 25 °C	2.6 ^{b, c}	
Single Pulse Avalanche Current	I _{AS}	20		
Single Pulse Avalanche Energy	E _{AS}	20	mJ	
Maximum Power Dissipation	P _D	T _C = 25 °C	5.9	W
		T _C = 70 °C	3.8	
		T _A = 25 °C	3.1 ^{b, c}	
		T _A = 70 °C	2 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, †}	R _{thJA}	33	40	°C/W	
Maximum Junction-to-Foot (Drain)	R _{thJF}	17	21		

Notes:

- Based on T_C = 25 °C.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under steady state conditions is 80 °C/W.

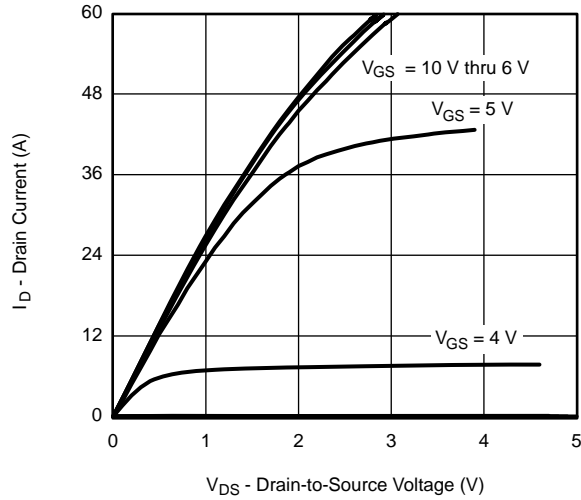
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		172		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 10		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		3.0	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		0.036	0.040	Ω
		$V_{GS} = 8\text{ V}, I_D = 5\text{ A}$		0.037	0.047	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 5\text{ A}$		23		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1735		pF
Output Capacitance	C_{oss}			160		
Reverse Transfer Capacitance	C_{rss}			37		
Total Gate Charge	Q_g	$V_{DS} = 75\text{ V}, V_{GS} = 10\text{ V}, I_D = 5\text{ A}$		28.5	43	nC
		$V_{DS} = 75\text{ V}, V_{GS} = 8\text{ V}, I_D = 5\text{ A}$		23	35	
Gate-Source Charge	Q_{gs}			8		
Gate-Drain Charge	Q_{gd}		6.5			
Gate Resistance	R_g	$f = 1\text{ MHz}$		0.85	1.3	Ω
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		14	21	ns
Rise Time	t_r			12	18	
Turn-Off Delay Time	$t_{d(off)}$			22	33	
Fall Time	t_f			6	10	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 8\text{ V}, R_g = 1\text{ }\Omega$		16	24	
Rise Time	t_r			12	18	
Turn-Off Delay Time	$t_{d(off)}$			20	30	
Fall Time	t_f			7	12	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			7.7	A
Pulse Diode Forward Current ^a	I_{SM}				50	
Body Diode Voltage	V_{SD}	$I_S = 2.6\text{ A}$		0.77	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		63	95	ns
Body Diode Reverse Recovery Charge	Q_{rr}			110	165	nC
Reverse Recovery Fall Time	t_a			49		ns
Reverse Recovery Rise Time	t_b			14		

Notes:

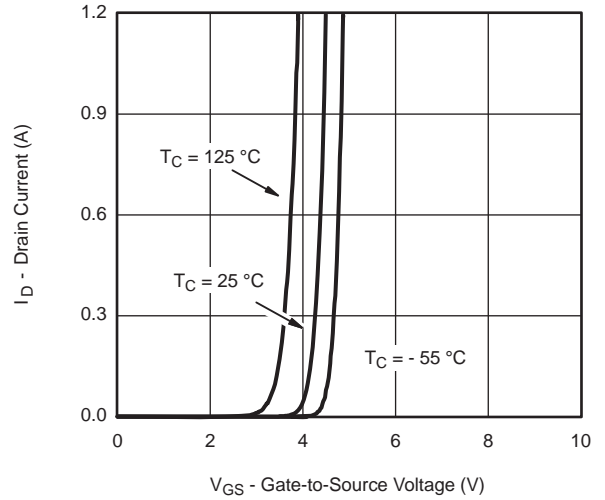
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
 a. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

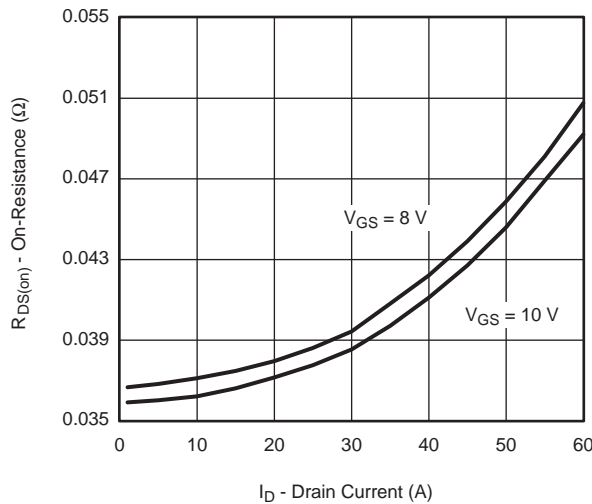
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



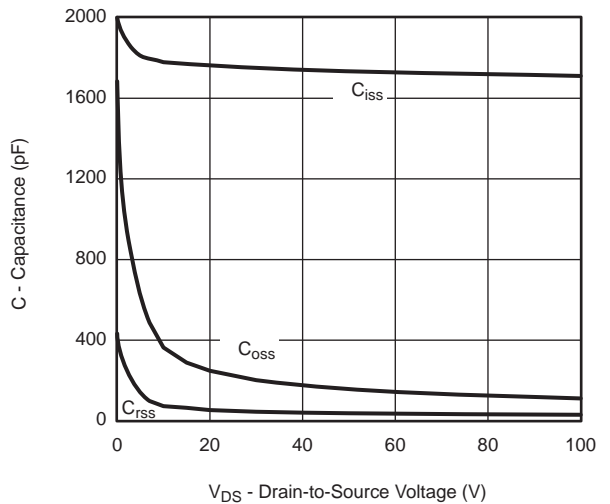
Output Characteristics



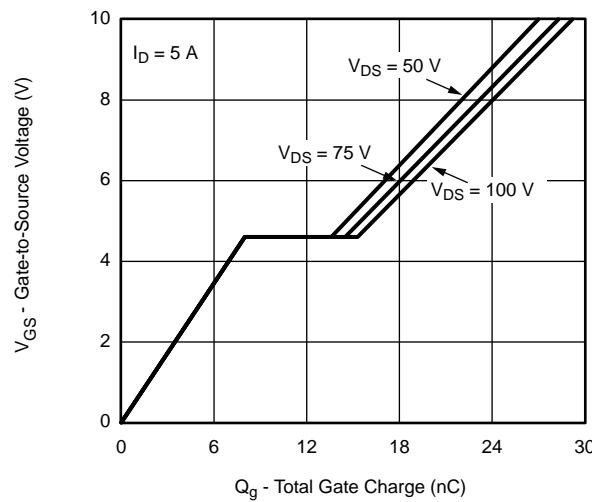
Transfer Characteristics



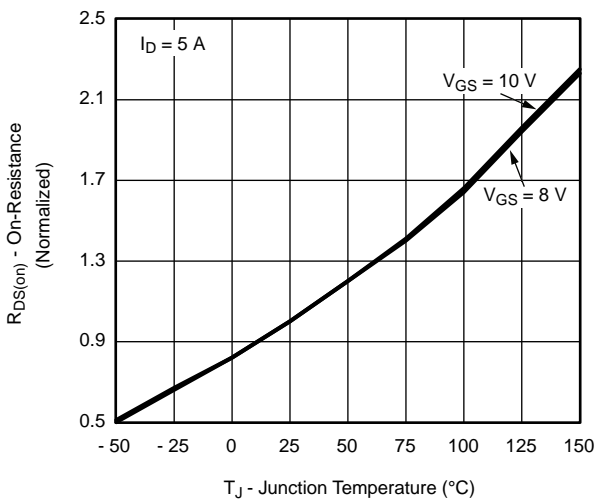
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

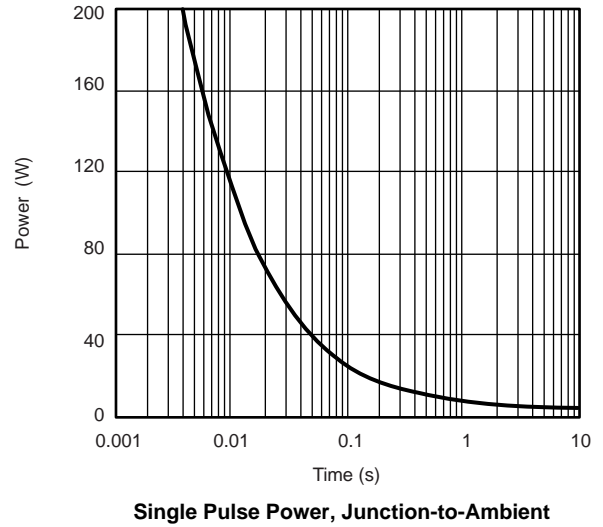
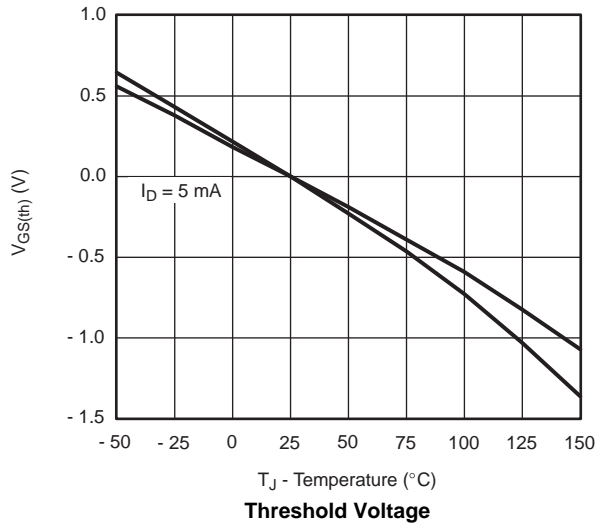


Gate Charge



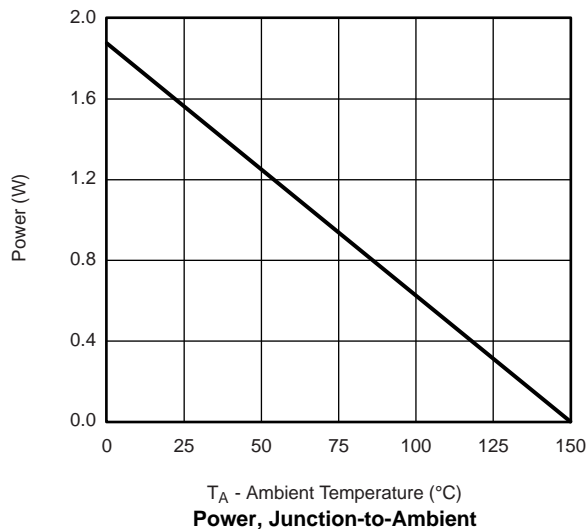
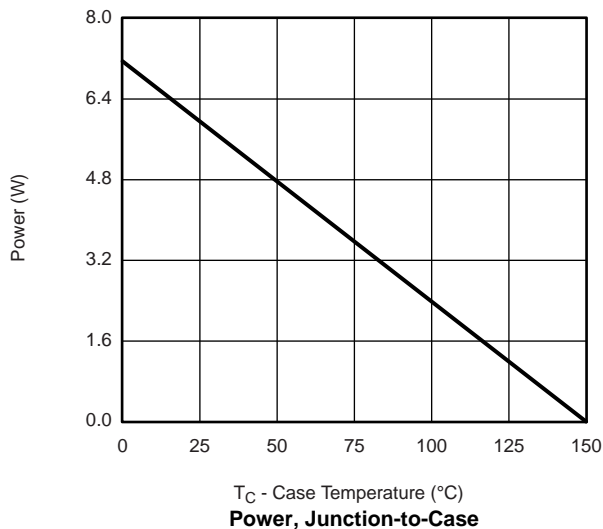
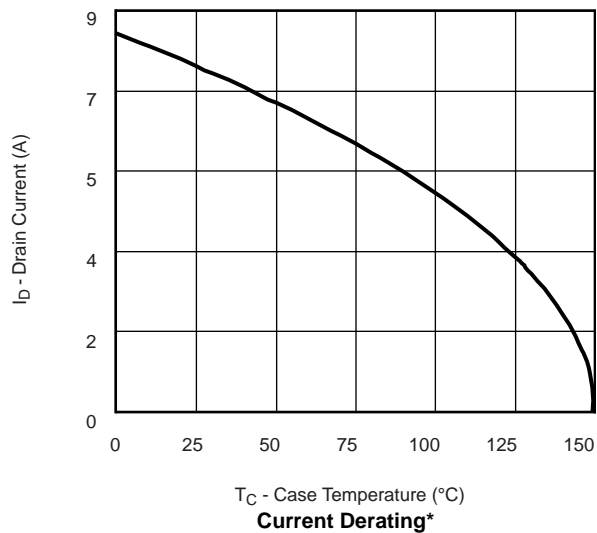
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



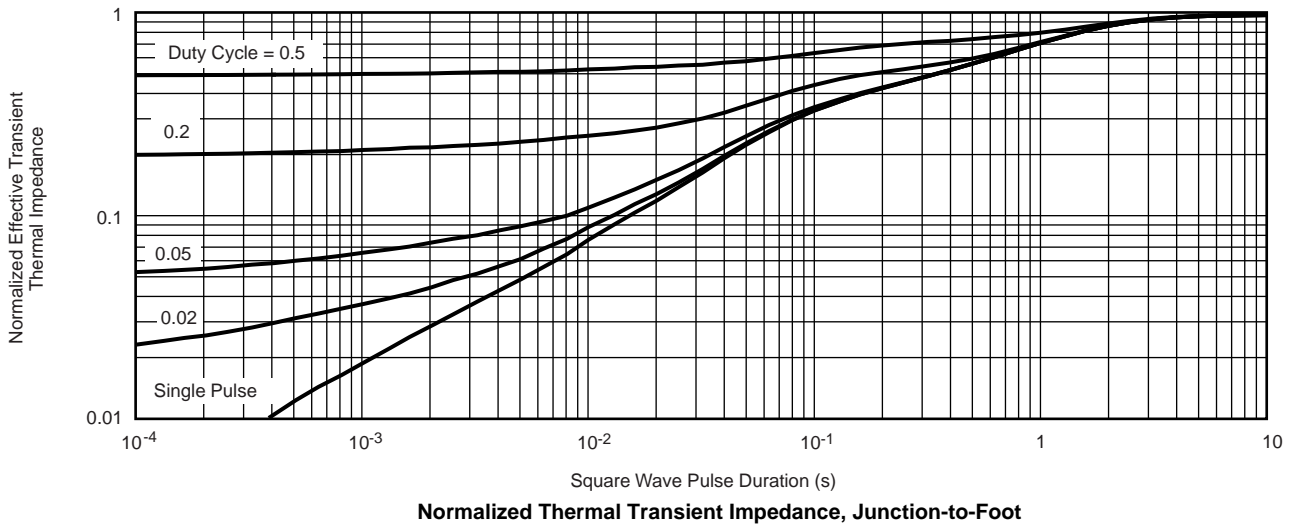
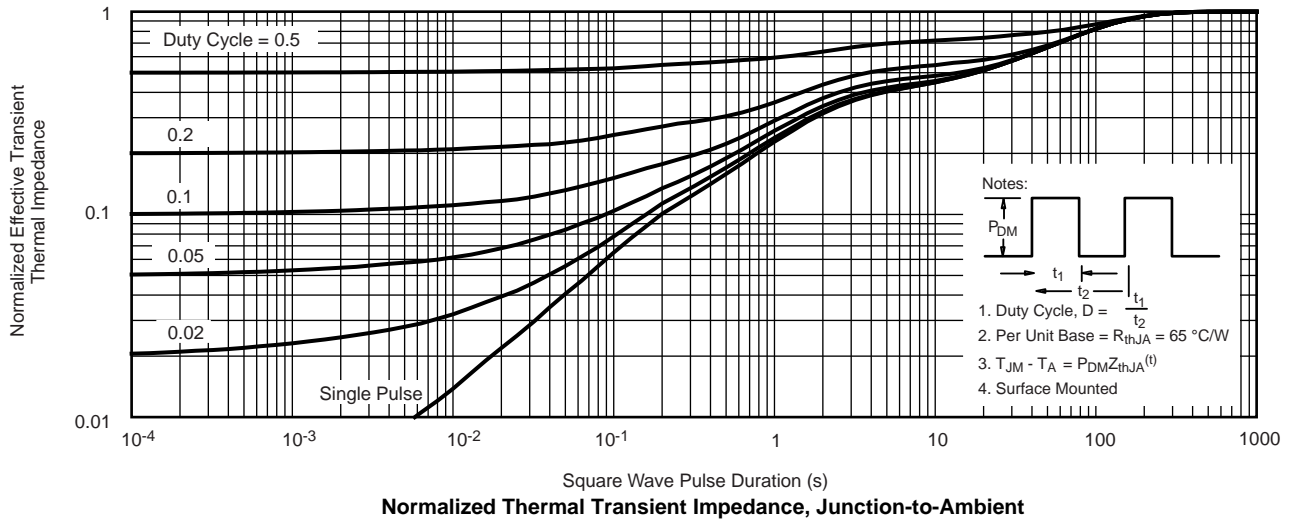
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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